

HAT2105T

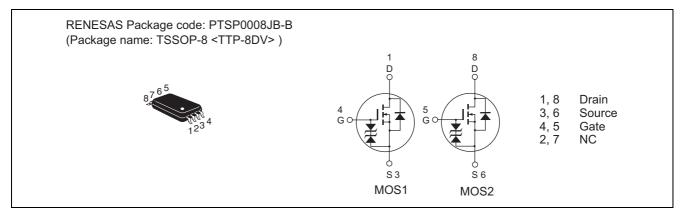
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G0384-0200 Rev.2.00 Aug 06, 2007

Features

- Low on-resistance
- Capable of 4 V gate drive
- High density mounting

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	200	V
Gate to source voltage	V _{GSS}	±15	V
Drain current	I _D	0.5	A
Drain peak current	I _D (pulse) ^{Note1}	2	A
Body-drain diode reverse drain current	I _{DR}	0.5	A
Channel dissipation	Pch ^{Note 2}	1	W
	Pch ^{Note 3}	1.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1 %

2. 1 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10 s

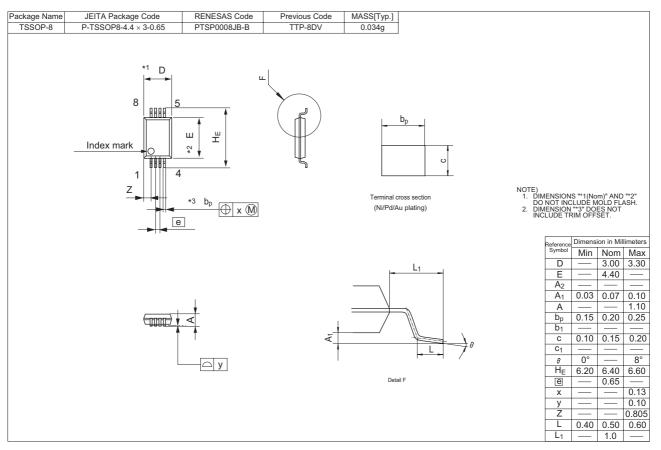
3. 2 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10 s

Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	200	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	V _{(BR)GSS}	±15	—	—	V	$I_G=\pm 100~\mu A,~V_{DS}=0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS}=\pm 12~V,~V_{DS}=0$
Zero gate voltage drain current	I _{DSS}	_	_	5	μΑ	$V_{DS} = 200 V, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	1.0	_	2.1	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	1.6	2.2	Ω	$I_D = 0.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R _{DS(on)}	_	1.9	2.7	Ω	$I_D = 0.5 \text{ A}, V_{GS} = 4 \text{ V}^{Note4}$
	R _{DS(on)}	_	2.4	5.5	Ω	$I_D = 2 \text{ A}, V_{GS} = 5 \text{ V}^{Note4}$
Forward transfer admittance	y _{fs}	0.56	0.86	—	S	$I_D = 0.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	120	—	pF	V _{DS} = 10 V
Output capacitance	Coss	_	29	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	10	—	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	—	10	—	ns	$V_{GS} = 5 \text{ V}, \text{ I}_{D} = 0.5 \text{ A}$
Rise time	tr	—	14	—	ns	$V_{DD}\cong 30~V$
Turn-off delay time	t _{d(off)}	—	24	—	ns	
Fall time	t _f		9	_	ns	
Body-drain diode forward voltage	V _{DF}		0.9	1.4	V	$I_F = 0.5 \text{ A}, V_{GS} = 0^{Note4}$

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
HAT2105T-EL-E	3000 pcs	Taping

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